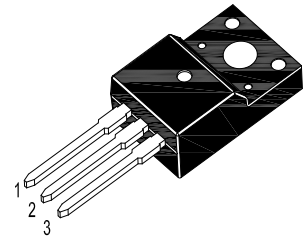


2SA1049

PNP Silicon Epitaxial Planar Transistor

Features

- Low Collector Emitter Saturation Voltage



TO-220F Plastic Package

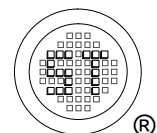
1.Base 2.Collector 3.Emitter

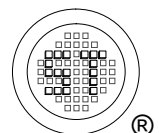
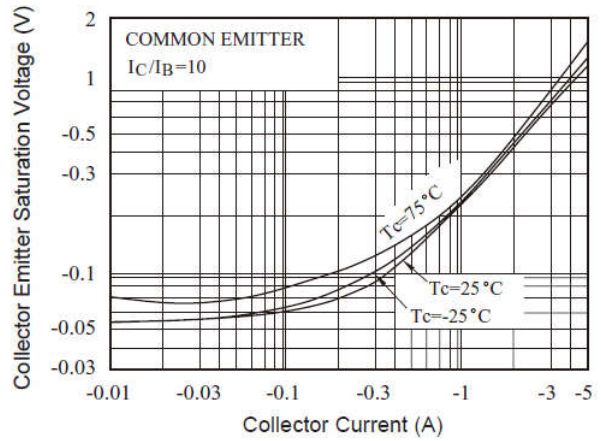
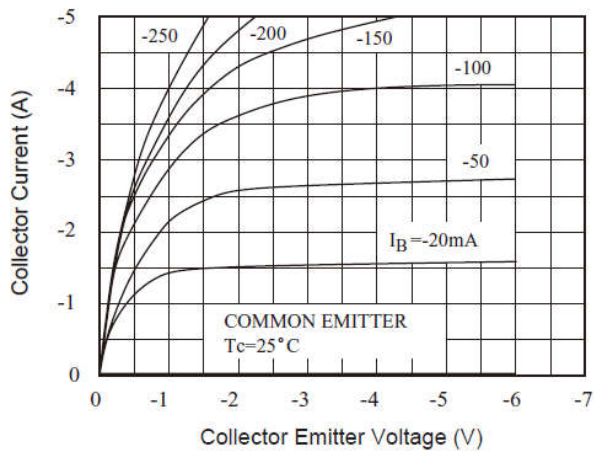
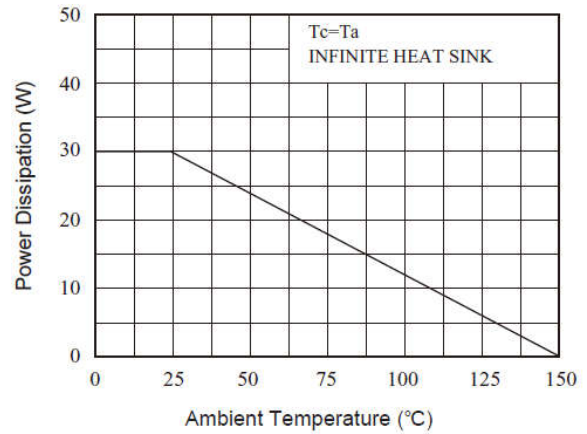
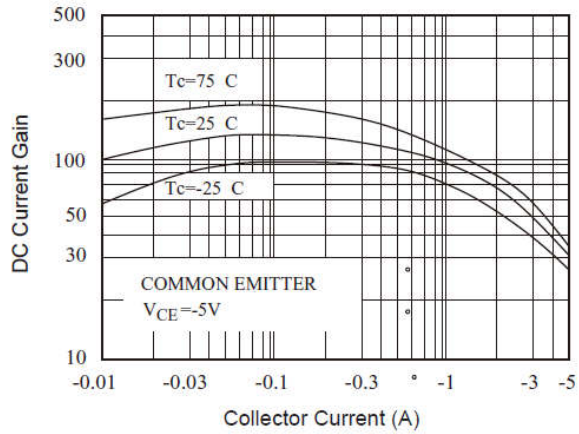
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	100	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	100	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	5	A
Base Current	$-I_{\text{B}}$	0.5	A
Power Dissipation ($T_c = 25^\circ\text{C}$)	P_{D}	30	W
Junction Temperature	T_{j}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{\text{CE}} = 5 \text{ V}$, $-I_{\text{C}} = 1 \text{ A}$ at $-V_{\text{CE}} = 5 \text{ V}$, $-I_{\text{C}} = 4 \text{ A}$	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
	h_{FE}	20	-	-	-	
Collector Base Cutoff Current at $-V_{\text{CB}} = 100 \text{ V}$	$-I_{\text{CBO}}$	-	-	100	μA	
Emitter Base Cutoff Current at $-V_{\text{EB}} = 5 \text{ V}$	$-I_{\text{EBO}}$	-	-	1	mA	
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 50 \text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	100	-	-	V	
Collector Emitter Saturation Voltage at $-I_{\text{C}} = 4 \text{ A}$, $-I_{\text{B}} = 0.4 \text{ A}$	$-V_{\text{CE}(\text{sat})}$	-	-	2	V	
Base Emitter Voltage at $-V_{\text{CE}} = 5 \text{ A}$, $-I_{\text{C}} = 4 \text{ A}$	$-V_{\text{BE}}$	-	-	1.5	V	
Transition Frequency at $-V_{\text{CE}} = 5 \text{ V}$, $-I_{\text{C}} = 1 \text{ A}$	f_{T}	-	30	-	MHz	
Collector Output Capacitance at $-V_{\text{CB}} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	90	-	pF	





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Package Outline(Dimension in mm)

TO-220F

